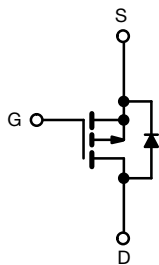
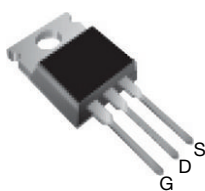


## Power MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	-100	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = -10$ V	0.30
$Q_g$ max. (nC)	38	
$Q_{gs}$ (nC)	6.8	
$Q_{gd}$ (nC)	21	
Configuration	Single	

**TO-220AB**


P-Channel MOSFET

### FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- P-channel
- 175 °C operating temperature
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.


**RoHS\***  
Available

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF9530PbF
	SiHF9530-E3
SnPb	IRF9530
	SiHF9530

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V <sub>DS</sub>	-100	V
Gate-Source Voltage			V <sub>GS</sub>	± 20	
Continuous Drain Current	V <sub>GS</sub> at - 10 V	T <sub>C</sub> = 25 °C	I <sub>D</sub>	- 12	A
		T <sub>C</sub> = 100 °C		-8.2	
Pulsed Drain Current <sup>a</sup>			I <sub>DM</sub>	-48	
Linear Derating Factor				0.59	W/°C
Single Pulse Avalanche Energy <sup>b</sup>			E <sub>AS</sub>	400	mJ
Repetitive Avalanche Current <sup>a</sup>			I <sub>AR</sub>	-12	A
Repetitive Avalanche Energy <sup>a</sup>			E <sub>AR</sub>	8.8	mJ
Maximum Power Dissipation		T <sub>C</sub> = 25 °C	P <sub>D</sub>	88	W
Peak Diode Recovery dV/dt <sup>c</sup>			dV/dt	- 5.5	V/ns
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering Recommendations (Peak temperature) <sup>d</sup>		for 10 s		300	
Mounting Torque	6-32 or M3 screw			10	
				1.1	N · m

### Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b.  $V_{DD} = -25$  V, starting  $T_J = 25$  °C,  $L = 4.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = -12$  A (see fig. 12).

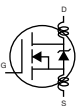

c.  $I_{SD} \leq -12$  A,  $dI/dt \leq 140$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175$  °C.

d. 1.6 mm from case.

**THERMAL RESISTANCE RATINGS**

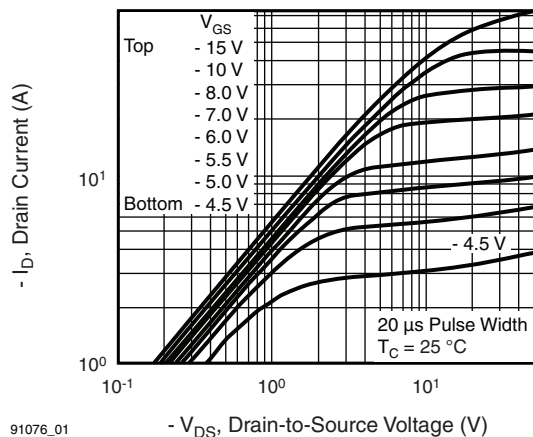
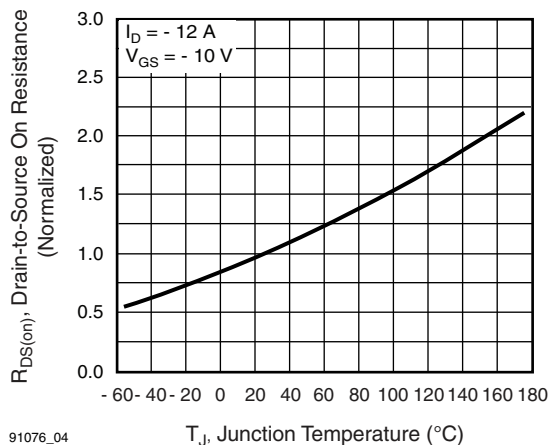
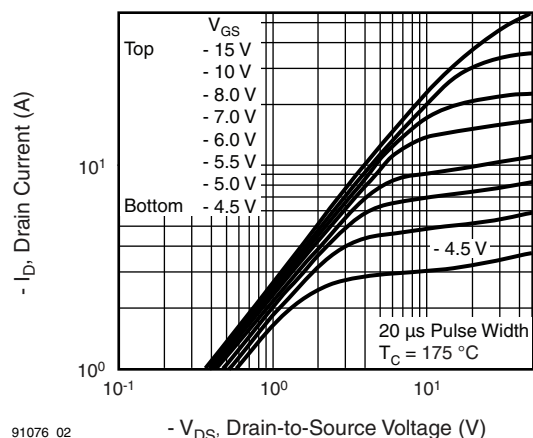
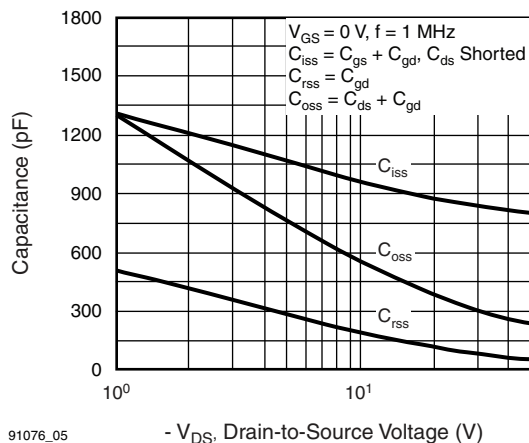
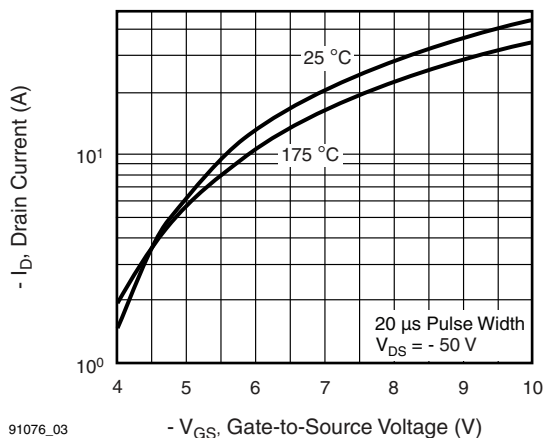
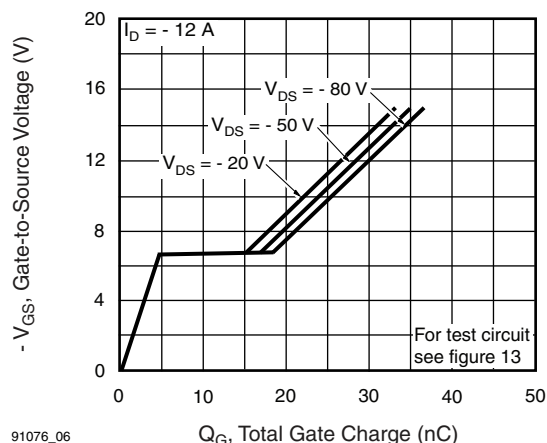
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.7	

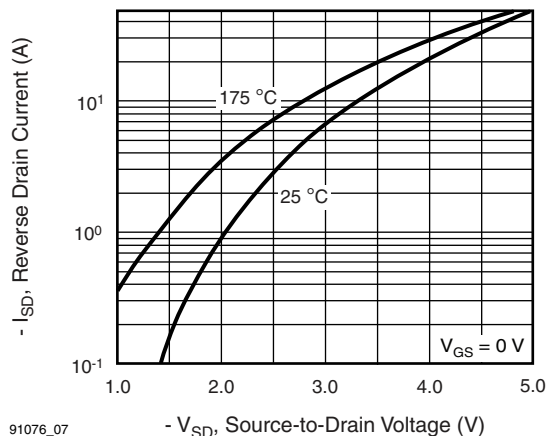
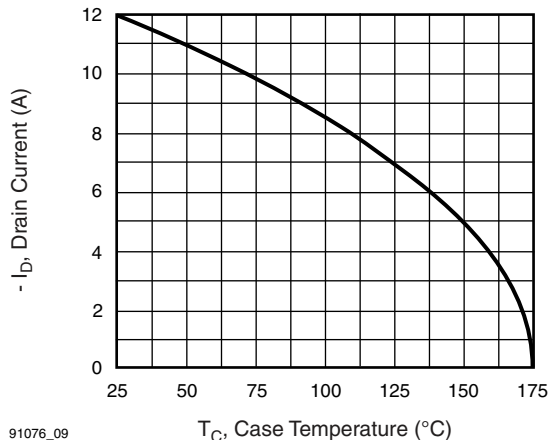
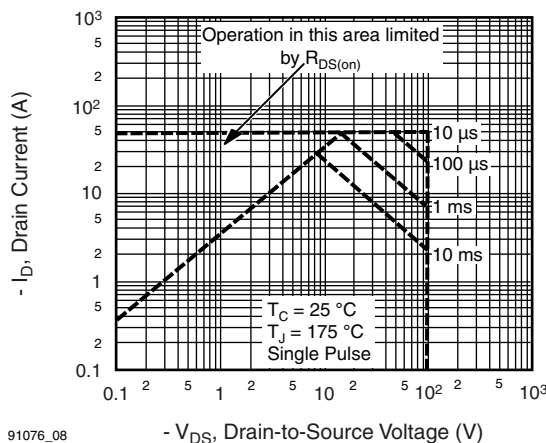
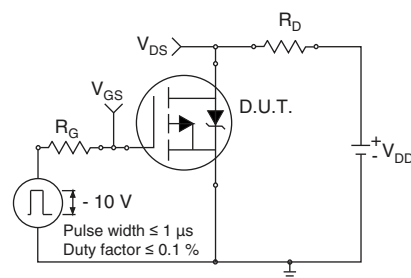
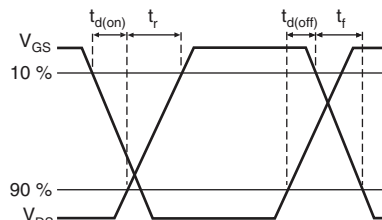
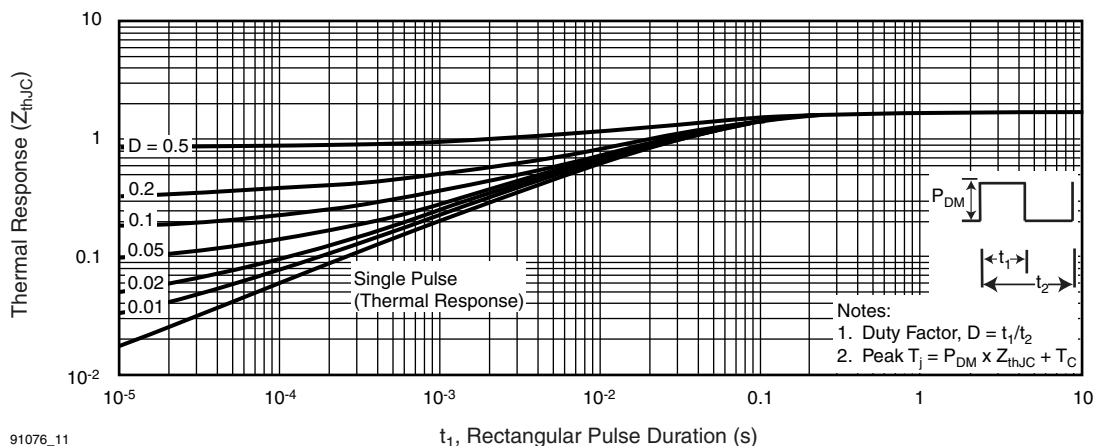
**SPECIFICATIONS** ( $T_J = 25\text{ °C}$ , unless otherwise noted)

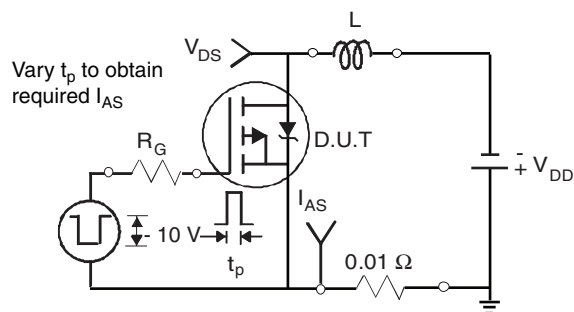
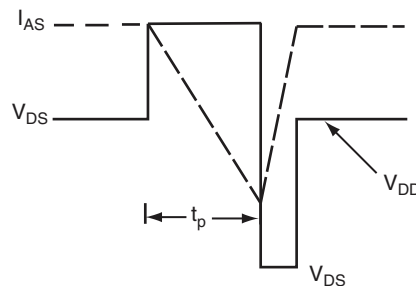
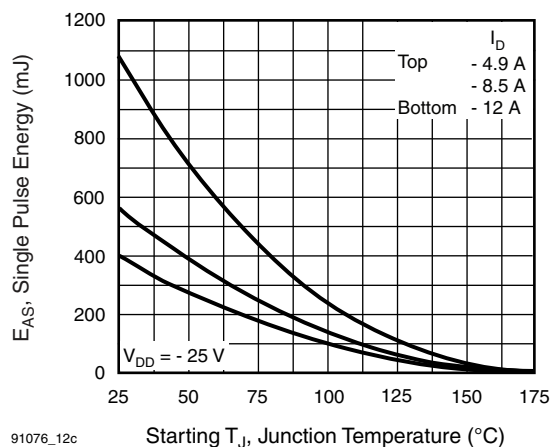
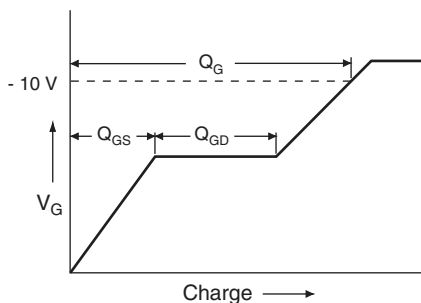
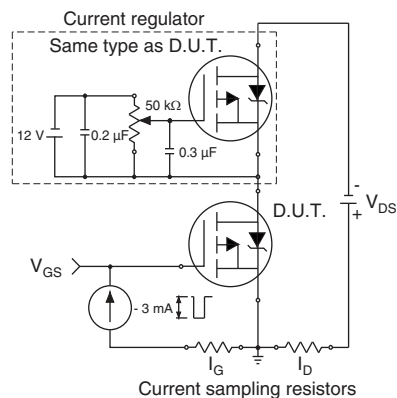
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = -250\text{ }\mu\text{A}$	-100	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ °C}$ , $I_D = -1\text{ mA}$	-	-0.10	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\text{ }\mu\text{A}$	-2.0	-	-4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -100\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	-100	$\mu\text{A}$
		$V_{DS} = -80\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 150\text{ °C}$	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$ , $I_D = -7.2\text{ A}^b$	-	-	0.30	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = -50\text{ V}$ , $I_D = -7.2\text{ A}^b$	3.7	-	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = -25\text{ V}$ , $f = 1.0\text{ MHz}$ , see fig. 5	-	860	-	pF
Output Capacitance	$C_{oss}$		-	340	-	
Reverse Transfer Capacitance	$C_{rss}$		-	93	-	
Total Gate Charge	$Q_g$	$V_{GS} = -10\text{ V}$ , $I_D = -12\text{ A}$ , $V_{DS} = -80\text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	-	38	nC
Gate-Source Charge	$Q_{gs}$		-	-	6.8	
Gate-Drain Charge	$Q_{gd}$		-	-	21	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}$ , $I_D = -12\text{ A}$ , $R_g = 12\text{ }\Omega$ , $R_D = 3.9\text{ }\Omega$ , see fig. 10 <sup>b</sup>	-	12	-	ns
Rise Time	$t_r$		-	52	-	
Turn-Off Delay Time	$t_{d(off)}$		-	31	-	
Fall Time	$t_f$		-	39	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	$L_S$		-	7.5	-	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}$ , open drain	0.4	-	3.3	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p-n junction diode 	-	-	-12	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	-48	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ °C}$ , $I_S = -12\text{ A}$ , $V_{GS} = 0\text{ V}^b$	-	-	-6.3	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ °C}$ , $I_F = -12\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	120	240	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	0.46	0.92	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )				

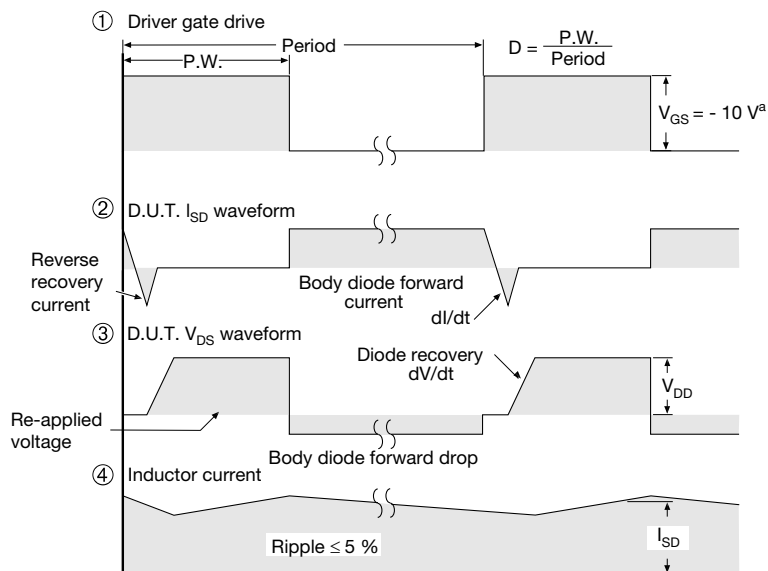
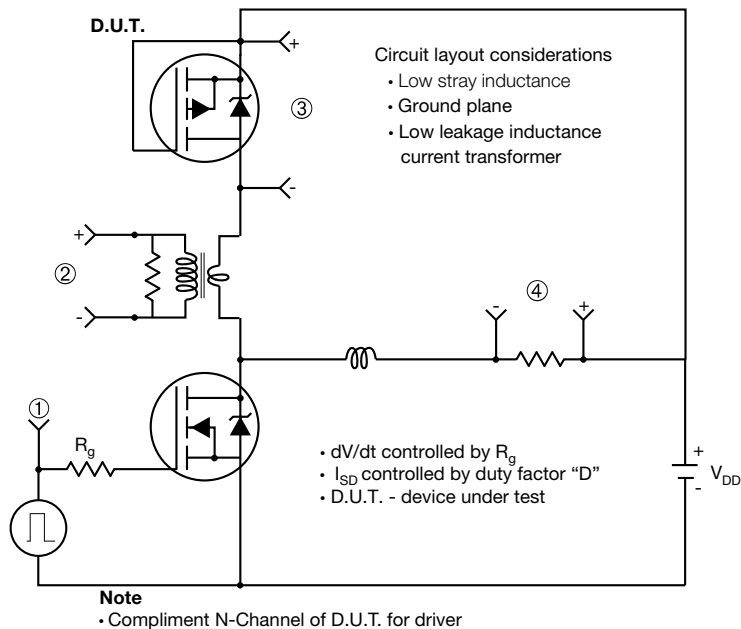
**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$** 

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics,  $T_C = 175^\circ\text{C}$** 

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Maximum Safe Operating Area**

**Fig. 10a - Switching Time Test Circuit**

**Fig. 10b - Switching Time Waveforms**

**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**


**Fig. 12a - Unclamped Inductive Test Circuit**

**Fig. 12b - Unclamped Inductive Waveforms**

**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**

**Fig. 13a - Basic Gate Charge Waveform**

**Fig. 13b - Gate Charge Test Circuit**

**Peak Diode Recovery  $dV/dt$  Test Circuit**

**Note**

a.  $V_{GS} = -5V$  for logic level and  $-3V$  drive devices

**Fig. 14 -For P-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?91076](http://www.vishay.com/ppg?91076).

## TO-220-1



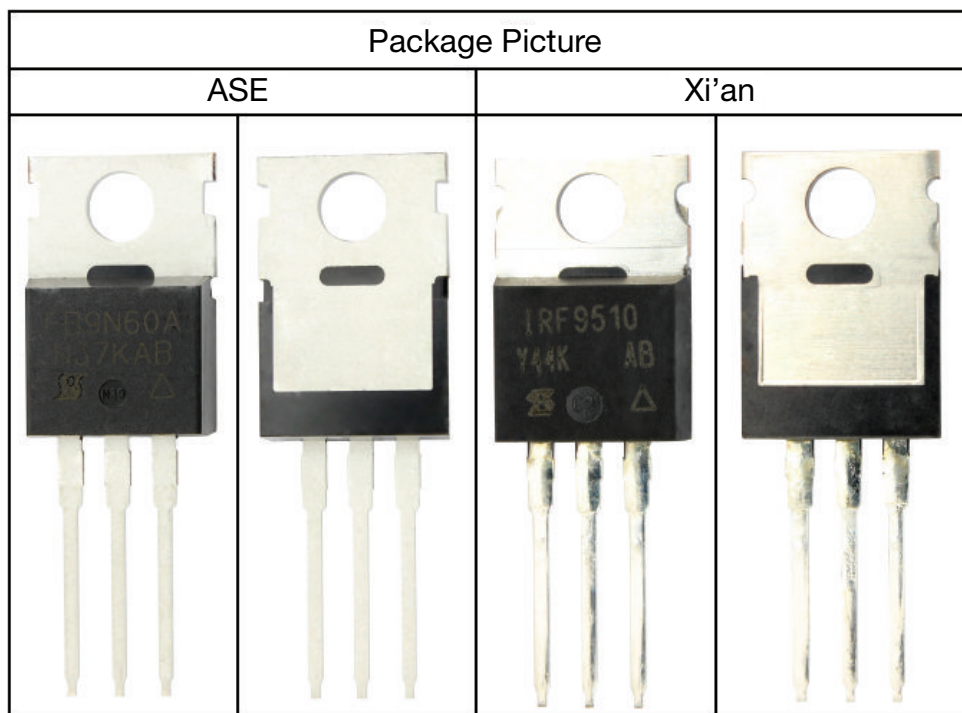
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15  
DWG: 6031

### Note

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM

## Package Picture





## Disclaimer

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